Complementary Silicon Power Transistors

MJE270G (NPN), MJE271G (PNP)

Features

- High Safe Operating Area I_{S/B} @ 40 V, 1.0 s = 0.375 A
- Collector–Emitter Sustaining Voltage V_{CEO(sus)} = 100 Vdc (Min)
- High DC Current Gain h_{FE} @ 120 mA, 10 V = 1500 (Min)
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 100 | Vdc |
| Collector-Base Voltage | V _{CB} | 100 | Vdc |
| Emitter-Base Voltage | V _{EB} | 5.0 | Vdc |
| Collector Current – Continuous | Ι _C | 2.0 | Adc |
| Collector Current – Peak | I _{CM} | 4.0 | Adc |
| Base Current | Ι _Β | 0.1 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | P _D | 15 0.12 | W W/°C |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | P _D | 1.5 0.012 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

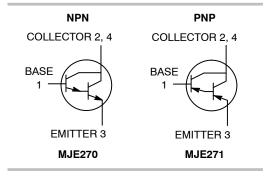
| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 8.33 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 83.3 | °C/W |



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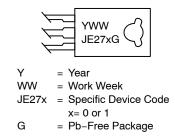
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2.0 AMPERE COMPLEMENTARY POWER DARLINGTON TRANSISTORS 100 VOLTS, 15 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

| Device | Package | Shipping |
|----------|---------------------|-----------------|
| MJE270G | TO–225 (Pb–Free) | 500 Units / Box |
| MJE270TG | TO–225 (Pb–Free) | 50 Units / Rail |
| MJE271G | TO–225 (Pb–Free) | 500 Units / Box |

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|-----------------------|-------------|------------|------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Sustaining Voltage (Note 1) $(I_{C} = 10 \text{ mAdc}, I_{B} = 0)$ | V _{CEO(sus)} | 100 | - | Vdc |
| Collector Cutoff Current ($V_{CE} = 100 \text{ Vdc}, I_B = 0$) | I _{CEO} | - | 1.0 | mAdc |
| Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}, I_E = 0$) | I _{CBO} | - | 0.3 | mAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | - | 0.1 | mAdc |
| SECOND BREAKDOWN | | | | |
| Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 40 Vdc, t = 1.0 s, Non-repetitive) | I _{S/b} | 375 | - | Adc |
| ON CHARACTERISTICS (Note 1) | | | | |
| DC Current Gain (I _C = 20 mAdc, V _{CE} = 3.0 Vdc) (I _C = 120 mAdc, V _{CE} = 10 Vdc) | h _{FE} | 500 1500 | | - |
| Collector–Emitter Saturation Voltage ($I_C = 20 \text{ mAdc}, I_B = 0.2 \text{ mAdc}$) ($I_C = 120 \text{ mAdc}, I_B = 1.2 \text{ mAdc}$) | V _{CE(sat)} | | 2.0 3.0 | Vdc |
| Base-Emitter On Voltage (I _C = 120 mAdc, V _{CE} = 10 Vdc) | V _{BE(on)} | - | 2.0 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Current Gain – Bandwidth Product (Note 2) (I _C = 0.05 Adc, V _{CE} = 5.0 Vdc, f _{test} = 1.0 MHz) | f _T | 6.0 | _ | MHz |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.

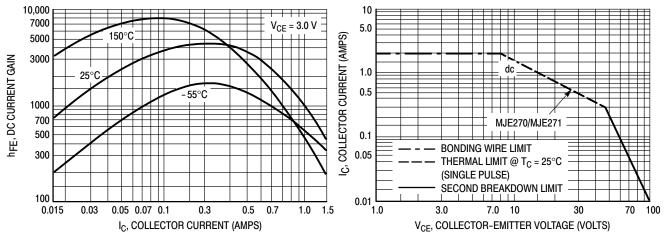


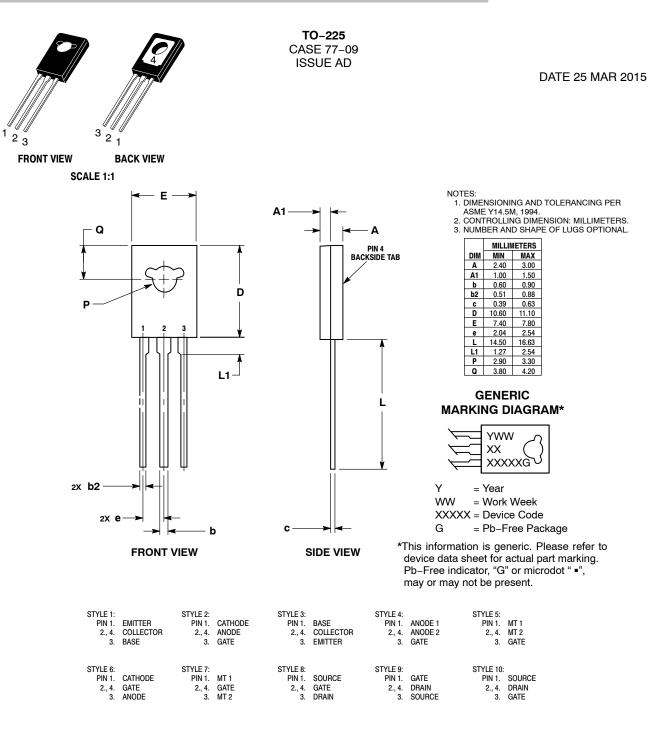


Figure 2. Safe Operating Area

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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